ACT Node
Standard Recipes

Resist	ARP 6200	Sample Prep for Resist spin	
Tone	Positive Tone Resist	Cleaning Solution	Sonicate
Solid content	13%, 9%	Acetone	2~5 min
Developer	AR 600 546 (n-Amyl Acetate)	IPA	2~5 min
Stopper	ISO-Propanol	Ethanol (optional)	2~5 min
Remover	Di-Methyl Acetate	DI Water Rinse	2~5 min
Thinner	Anisole	Bake	5 min
Adhesion Promoter	AR 300 80		

Spin	Speed	Thickness	Time
	4000rpm	350~380nm	60 s
Pre-Bake	**Temperature**		
	150 °C	if Hot Plate used	2 min
	150 °C	if oven used	30 min
Exposure	**Voltage**	**Base Dose**	
	20 ~ 30kv	65 (uC/cm2) [can vary between as per resist thickness 60-120]	
Develop	ZEP developer	Dipping	1 min
Stopper	IPA	Dipping	30 ~ 60 s
Rinse	DI water	De-Ionised Water	30 s
Post Bake	**Temperature**	before etch (if required)	
	130 °C	Hot Plate	2 min
	130 °C	Oven	25 min
Remover	ZEP Remover	Time depends on the pattern size and thickness of resist	Soak for 30 ~ 40 min
		DI Water rinse	1 min

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